

Silicon PNP Power Transistors

2SB794 2SB795

DESCRIPTION

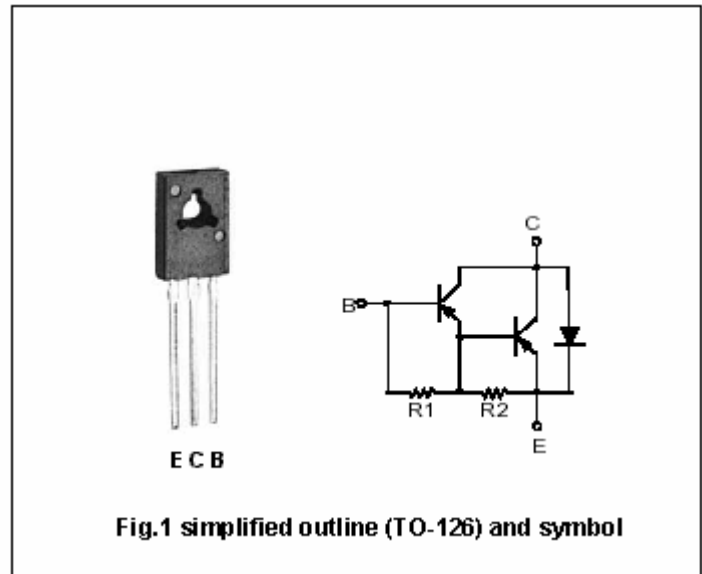
- With TO-126 package
- DARLINGTON
- High DC current gain
- Low collector saturation voltage
- Complement to type 2SD985 2SD986

APPLICATIONS

- For use in operating from IC without predriver ,such as hammer driver

PINNING(See Fig.2)

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base



Absolute maximum ratings(Ta=25□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	2SB794	-60	V
		2SB795	-80	
V _{CEO}	Collector-emitter voltage	2SB794	-60	V
		2SB795	-80	
V _{EBO}	Emitter-base voltage	Open collector	-8	V
I _C	Collector current (DC)		-1.5	A
I _{CM}	Collector current-peak		-3.0	A
P _D	Total power dissipation	T _a =25□	1.0	W
		T _C =25□	10	
T _j	Junction temperature		150	□
T _{stg}	Storage temperature		-55~150	□

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	2SB794	I _C =-10mA ; I _B =0	-60		V
		2SB795		-80		
V _{CEsat}	Collector-emitter saturation voltage	I _C =-1A ; I _B =-1mA			-1.5	V
V _{BEsat}	Base-emitter saturation voltage	I _C =-1A ; I _B =-1mA			-2.0	V
I _{CBO}	Collector cut-off current	2SB794	V _{CB} =-60V ; I _E =0		-1.0	μA
		2SB795		V _{CB} =-80V ; I _E =0		
I _{EBO}	Emitter cut-off current	V _{EB} =-5V ; I _C =0			-2.0	mA
h _{FE-1}	DC current gain	I _C =-0.5A ; V _{CE} =-2V	1000			
h _{FE-2}	DC current gain	I _C =-1A ; V _{CE} =-2V	2000		30000	

Switching times

t _{on}	Turn-on time	I _C =-1.0A ; I _{B1} =-I _{B2} =-1.0mA V _{CC} =-50V ; R _L =50Ω		0.5		μs
t _{stg}	Storage time			1.0		μs
t _f	Fall time			1.0		μs

◆ h_{FE-2} Classifications

M	L	K
2000-5000	4000-10000	8000-30000

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PACKAGE OUTLINE

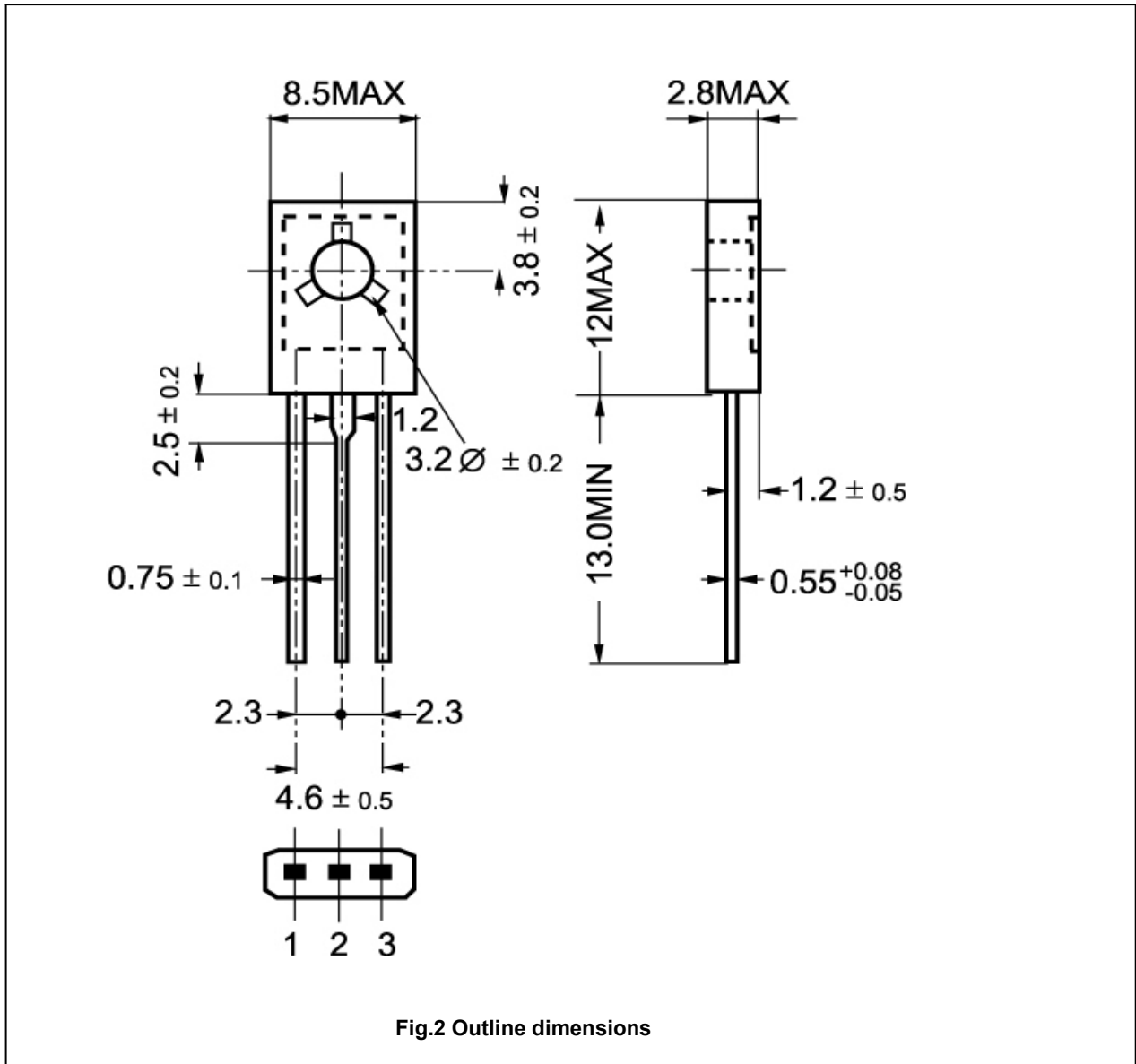


Fig.2 Outline dimensions